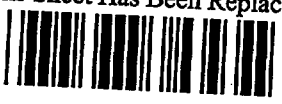
ULTRA - SHALLOW SEMICONDUCTOR JUNCTION FORMATION

ABSTRACT

A method for fabricating an ultra-shallow semi-conductor junction (24) using a high energy co-implantation step; a low energy dopant implantation step, and a fast isothermal annealing step is provided, Microelectronics devices such as FET and CMOS devices containing said ultra-shallow semiconductor junction (24) is also provided herein.

Fig 2d

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